



SHEET 1 OF 13

INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Substitute for form 1449/PTO)			ATTY. DOCKET NO. 061282-0234		SERIAL NO. 10/574,863	
			APPLICANT Yuichiro SASAKI, et al.			
			FILING DATE April 06, 2006		GROUP 2823	
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s) (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
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